

## N-Channel 30-V (D-S) MOSFET

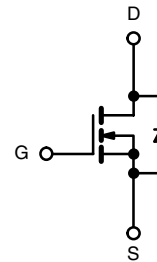
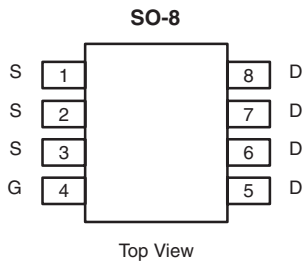
PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)
30	0.0042 at V <sub>GS</sub> = 10 V	28	29 nC
	0.0057 at V <sub>GS</sub> = 4.5 V	24	

### FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET<sup>®</sup> Power MOSFETs
- 100 % R<sub>g</sub> Tested



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available



N-Channel MOSFET

**Ordering Information:** Si4842BDY-T1-E3 (Lead (Pb)-free)  
Si4842BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	30	V	
Gate-Source Voltage	V <sub>GS</sub>	± 20		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	28	A
		T <sub>C</sub> = 70 °C	23	
		T <sub>A</sub> = 25 °C	20 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	16 <sup>b, c</sup>	
Pulsed Drain Current	I <sub>DM</sub>	60		
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	5.6	
		T <sub>A</sub> = 25 °C	2.7 <sup>b, c</sup>	
Single Pulse Avalanche Current	I <sub>AS</sub>	35	mJ	
Avalanche Energy	E <sub>AS</sub>	61		
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	6.25	W
		T <sub>C</sub> = 70 °C	4.0	
		T <sub>A</sub> = 25 °C	3.0 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	1.9 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>b, d</sup>	R <sub>thJA</sub>	32	42	°C/W	
Maximum Junction-to-Foot (Drain)	R <sub>thJF</sub>	15	20		

Notes:

- Based on T<sub>C</sub> = 25 °C.
- Surface Mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under Steady State conditions is 90 °C/W.

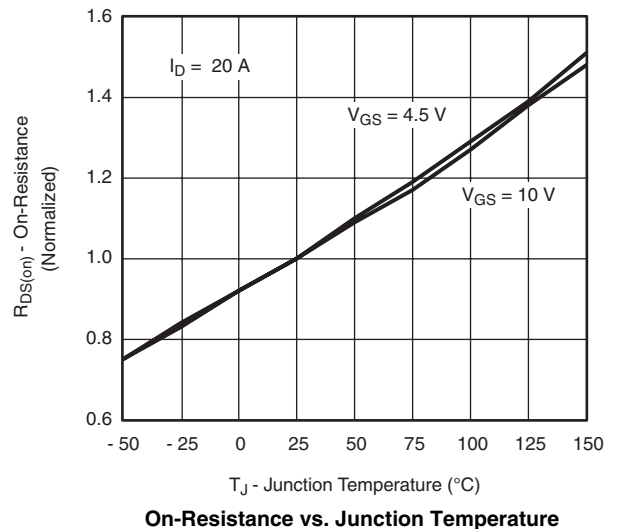
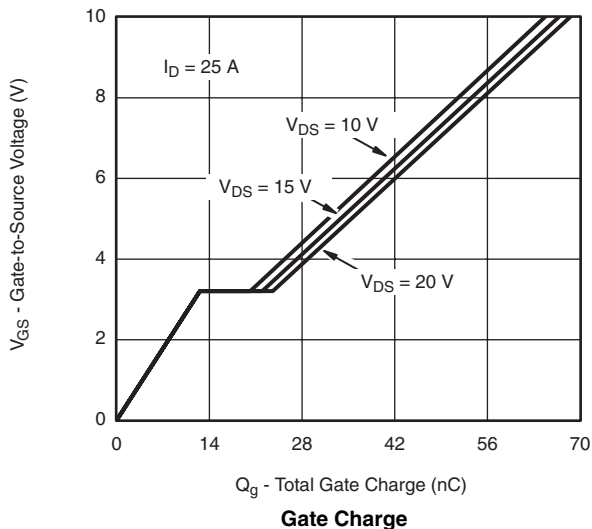
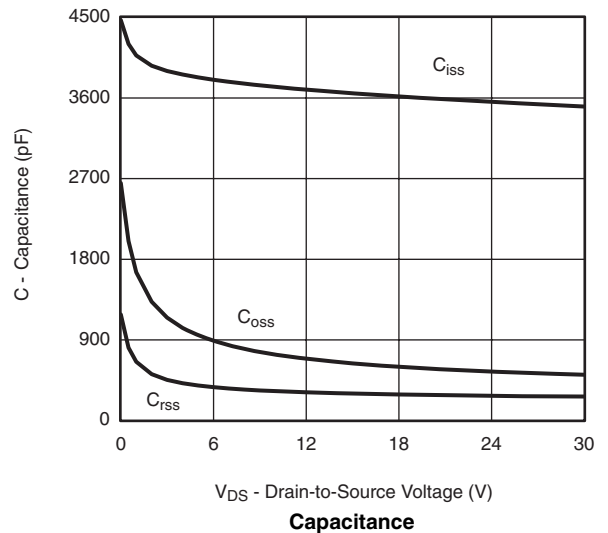
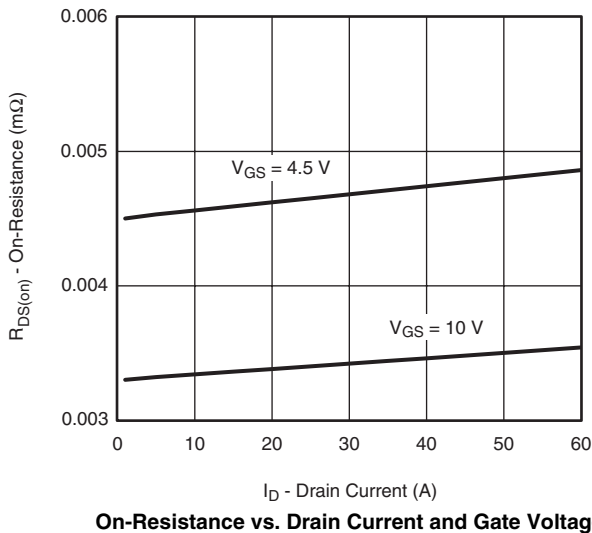
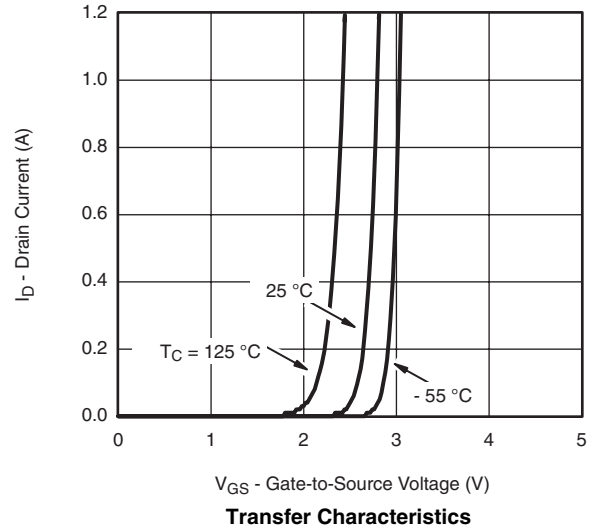
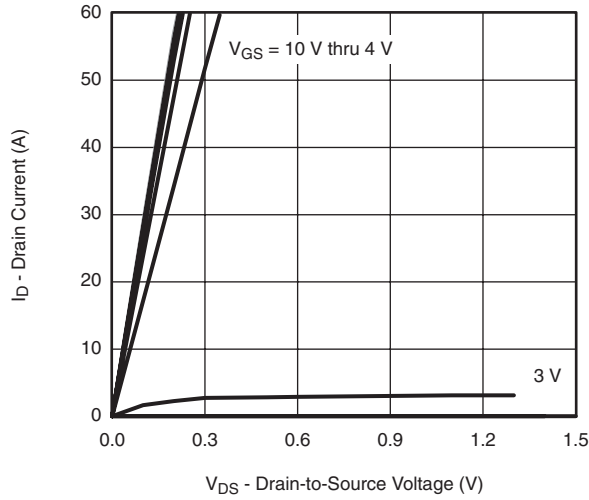
<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	30			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		30		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 6.4		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.4		3	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	30			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		0.0034	0.0042	$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 15\text{ A}$		0.0047	0.0057	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 20\text{ A}$		90		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		3650		$\mu\text{F}$
Output Capacitance	$C_{oss}$			635		
Reverse Transfer Capacitance	$C_{rss}$			300		
Total Gate Charge	$Q_g$	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 25\text{ A}$		68	100	nC
		$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 25\text{ A}$		29	43	
Gate-Source Charge	$Q_{gs}$		12.6			
Gate-Drain Charge	$Q_{gd}$		9.4			
Gate Resistance	$R_g$	$f = 1\text{ MHz}$		1.25	2	$\Omega$
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		125	190	ns
Rise Time	$t_r$			190	280	
Turn-Off Delay Time	$t_{d(off)}$			38	60	
Fall Time	$t_f$			13	20	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong 10\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		15	25	
Rise Time	$t_r$			15	25	
Turn-Off Delay Time	$t_{d(off)}$			42	65	
Fall Time	$t_f$			8	15	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			5.6	A
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				60	
Body Diode Voltage	$V_{SD}$	$I_S = 2.7\text{ A}$		0.74	1.1	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 10\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		34	55	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			31	50	nC
Reverse Recovery Fall Time	$t_a$			18		ns
Reverse Recovery Rise Time	$t_b$			16		

## Notes:

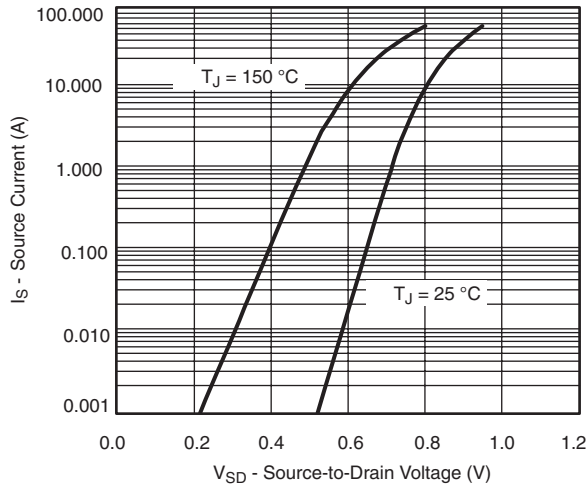
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$   
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

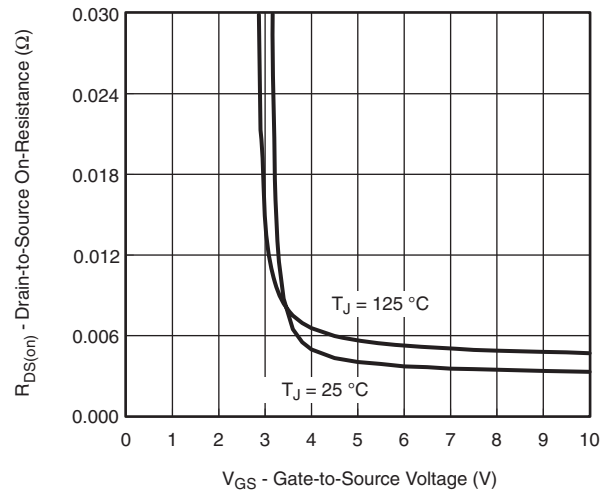
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



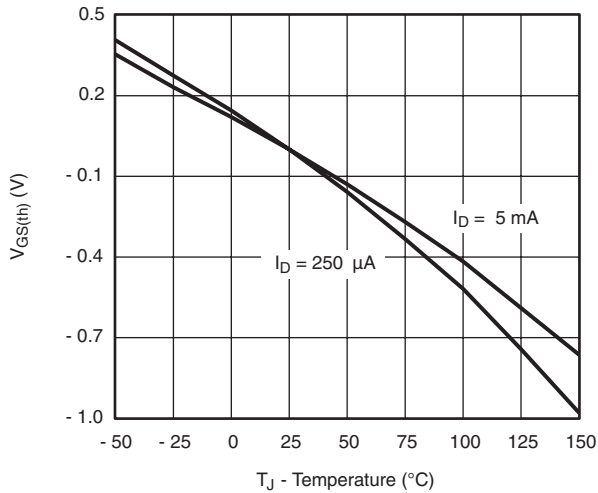
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



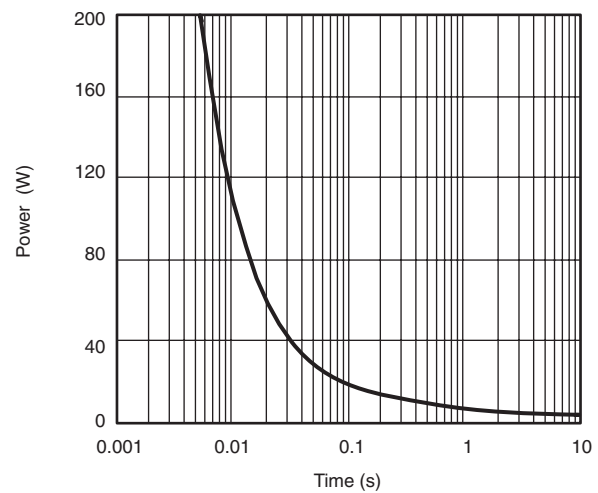
**Source-Drain Diode Forward Voltage**



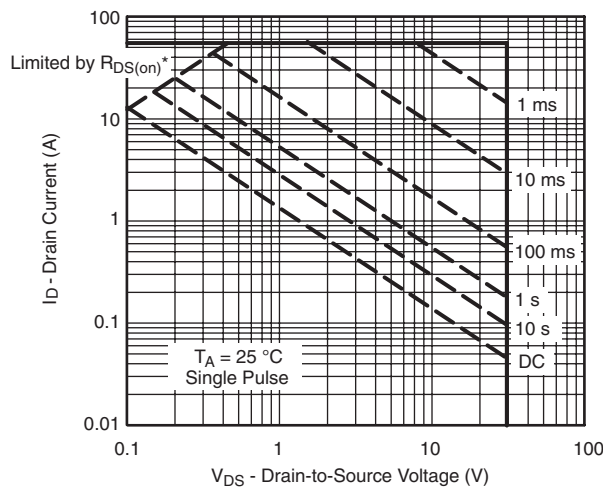
**On-Resistance vs. Gate-to-Source Voltage**



**Threshold Voltage**



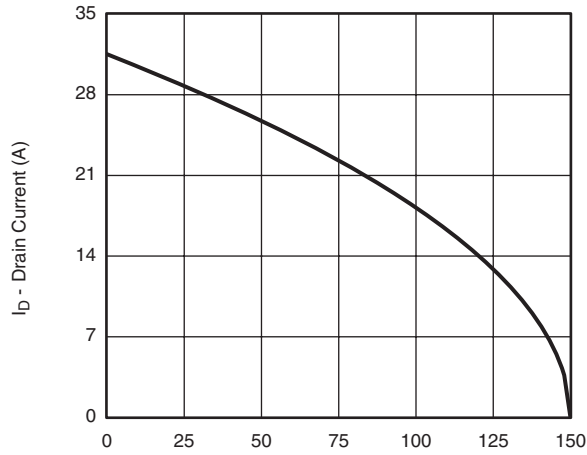
**Single Pulse Power, Junction-to-Ambient**



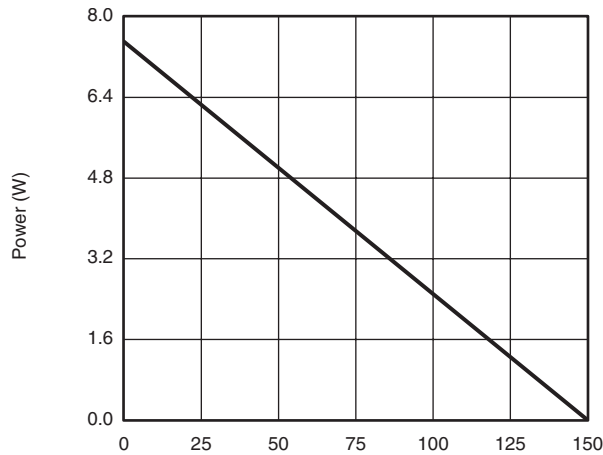
\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

**Safe Operating Area, Junction-to-Ambient**

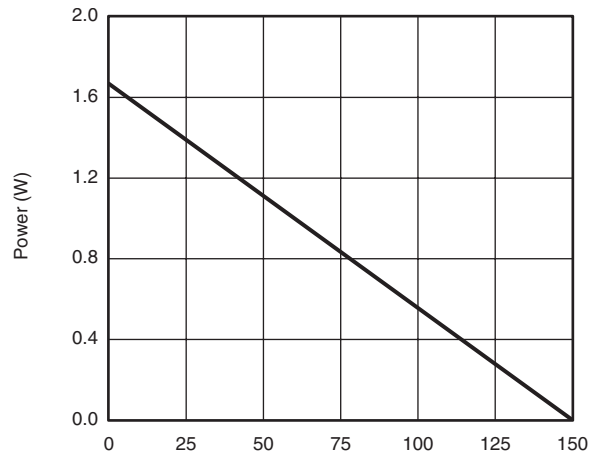
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



T<sub>C</sub> - Case Temperature (°C)  
**Current Derating\***



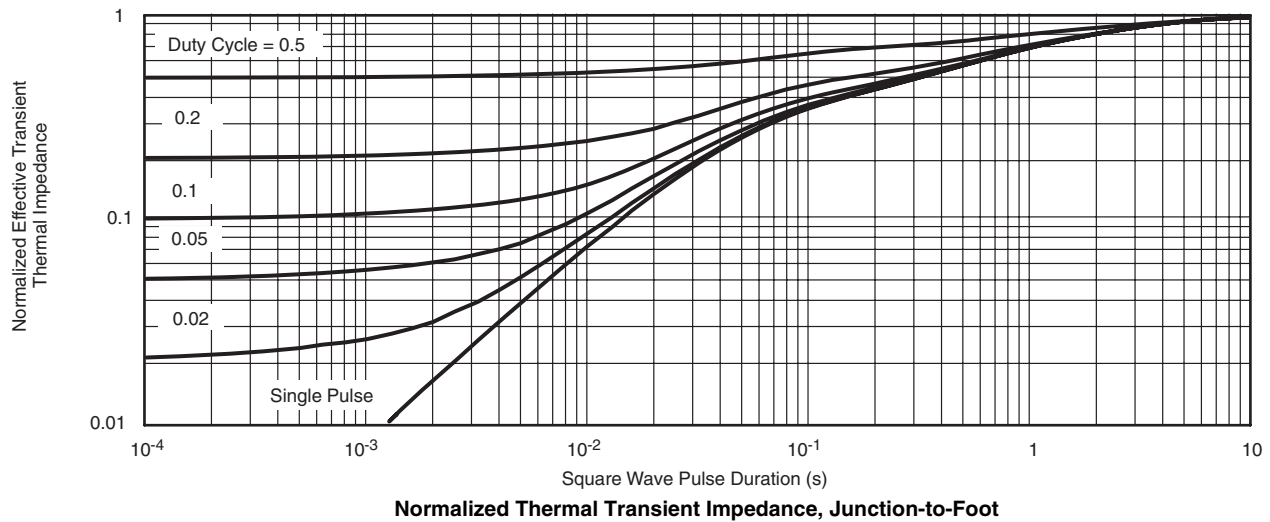
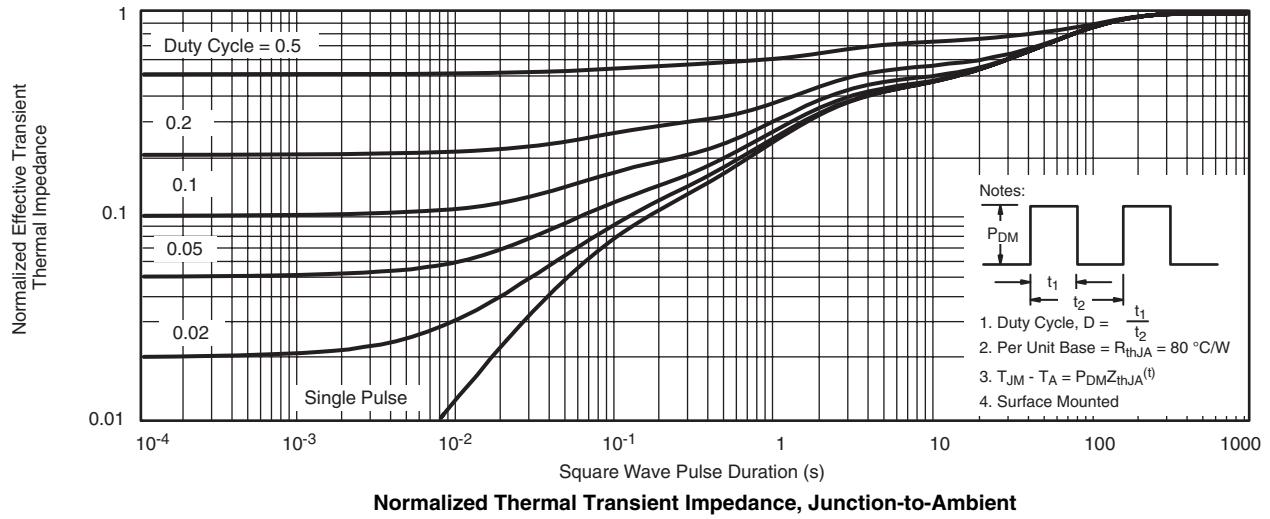
T<sub>C</sub> - Case Temperature (°C)  
**Power, Junction-to-Foot**



T<sub>A</sub> - Ambient Temperature (°C)  
**Power, Junction-to-Ambient**

\* The power dissipation P<sub>D</sub> is based on T<sub>J(max)</sub> = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



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## SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A <sub>1</sub>	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

## RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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